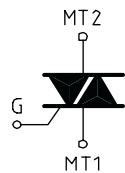
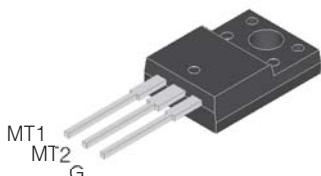


HIGH COMMUTATION TRIAC

TO220-F
(FULLY ISOLATED CASE)


On-State Current

25 Amp

Gate Trigger Current

≤ 50 mA

Off-State Voltage

200 V ÷ 800 V

This series of TRIACs uses a high performance PNPN technology.

These parts are intended for general purpose AC switching applications with highly inductive loads.

Absolute Maximum Ratings, according to IEC publication No. 134

SYMBOL	PARAMETER	CONDITIONS	Value	Unit
$I_{T(RMS)}$	RMS On-state Current (full sine wave)	All Conduction Angle, $T_c = 100^\circ\text{C}$	25	A
I_{TSM}	Non-repetitive On-State Current	Full Cycle, 60 Hz ($t = 16.7 \text{ ms}$)	215	A
I_{TSM}	Non-repetitive On-State Current	Full Cycle, 50 Hz ($t = 20 \text{ ms}$)	200	A
I^2t	Fusing Current	$t_p = 10 \text{ ms}$, Half Cycle	313	A^2s
I_{GM}	Peak Gate Current	$20 \mu\text{s}$ max. $T_j = 125^\circ\text{C}$	4	A
$P_{G(AV)}$	Average Gate Power Dissipation	$T_j = 125^\circ\text{C}$	1	W
dl / dt	Critical rate of rise of on-state current	$I_G = 2x I_{GT}$, $t_r \leq 100\text{ns}$ $f = 120 \text{ Hz}$, $T_j = 125^\circ\text{C}$	50	$\text{A}/\mu\text{s}$
T_j	Operating Temperature		(-40 +125)	$^\circ\text{C}$
T_{stg}	Storage Temperature		(-40 +150)	$^\circ\text{C}$
T_{sld}	Soldering Temperature	10s max	260	$^\circ\text{C}$
T_{iso}	R.M.S. isolation voltage 50/60 Hz sinusoidal waveform		2.500	Vac

SYMBOL	PARAMETER	VOLTAGE					Unit
		B	D	M	S	N	
V_{DRM}	Repetitive Peak Off State Voltage	200	400	600	700	800	V
V_{RRM}							

HIGH COMMUTATION TRIAC

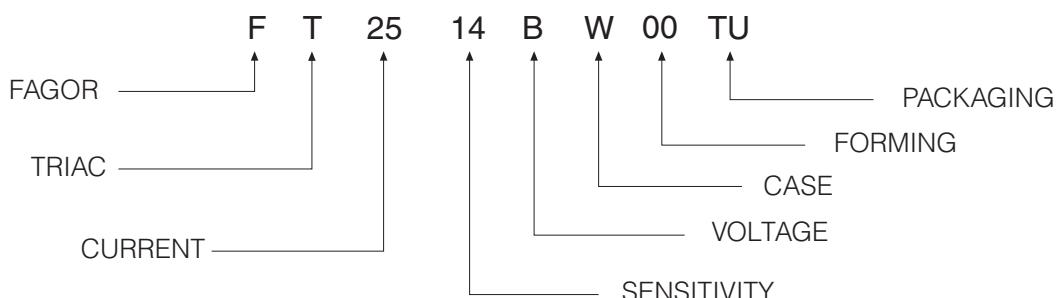
Electrical Characteristics

SYMBOL	PARAMETER	CONDITIONS	Quadrant	SENSITIVITY		Unit
				14	16	
$I_{GT}^{(1)}$	Gate Trigger Current	$V_D = 12 \text{ V}_{DC}$, $R_L = 33\Omega$, $T_j = 25^\circ\text{C}$	Q1÷Q3	MAX	35	mA
V_{GT}	Gate Trigger Voltage	$V_D = 12 \text{ V}_{DC}$, $R_L = 33\Omega$, $T_j = 25^\circ\text{C}$	Q1÷Q3	MAX	1.3	V
V_{GD}	Gate Non Trigger Voltage	$V_D = V_{DRM}$, $R_L = 3.3 \text{ K}\Omega$, $T_j = 125^\circ\text{C}$	Q1÷Q3	MIN	0.2	V
$I_H^{(2)}$	Holding Current	$I_T = 100 \text{ mA}$, Gate open, $T_j = 25^\circ\text{C}$		MAX	35	mA
I_L	Latching Current	$I_G = 1.2 I_{GT}$, $T_j = 25^\circ\text{C}$	Q1,Q3 Q2	MAX MAX	50 60	mA
$dV/dt^{(2)}$	Critical Rate of Voltage Rise	$V_D = 0.67 \times V_{DRM}$, Gate open $T_j = 125^\circ\text{C}$		MIN	500	$\text{V}/\mu\text{s}$
$(dI/dt)c^{(2)}$	Critical Rate of Current Rise	$(dI/dt)c = 0.1 \text{ V}/\mu\text{s}$ $T_j = 125^\circ\text{C}$ $(dI/dt)c = 10 \text{ V}/\mu\text{s}$ $T_j = 125^\circ\text{C}$ without snubber $T_j = 125^\circ\text{C}$		MIN MIN MIN	- - 13	A/ms
$V_{TM}^{(2)}$	On-state Voltage	$I_T = 35 \text{ Amp}$, $t_p = 380 \mu\text{s}$, $T_j = 25^\circ\text{C}$		MAX	1.55	V
$V_{t(o)}^{(2)}$	Threshold Voltage	$T_j = 125^\circ\text{C}$		MAX	0.85	V
$r_d^{(2)}$	Dynamic resistance	$T_j = 125^\circ\text{C}$		MAX	16	$\text{m}\Omega$
I_{DRM}/I_{RRM}	Off-State Leakage Current	$V_D = V_{DRM}$, $T_j = 125^\circ\text{C}$ $V_R = V_{RRM}$, $T_j = 25^\circ\text{C}$		MAX MAX	2 5	mA μA
$R_{th(j-c)}$	Thermal Resistance Junction-Case	for AC 360° conduction angle			2.5	$^\circ\text{C}/\text{W}$
$R_{th(j-a)}$	Thermal Resistance Junction-Ambient	$S = 1 \text{ cm}^2$			50	$^\circ\text{C}/\text{W}$

(1) Minimum I_{GT} is guaranteed at 5% of I_{GT} max.

(2) For either polarity of electrode MT2 voltage with reference to electrode MT1.

PART NUMBER INFORMATION



HIGH COMMUTATION TRIAC

Fig. 1: Maximum power dissipation versus RMS on-state current (full cycle)

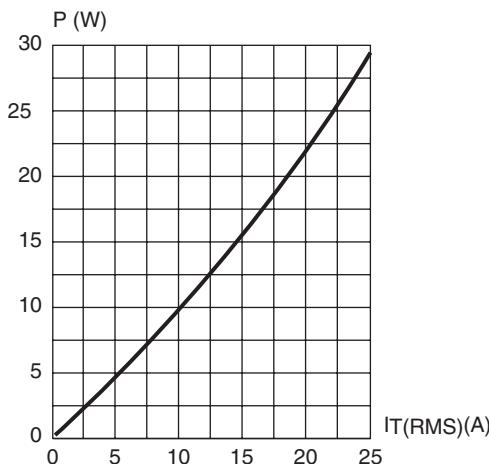


Fig. 2: RMS on-state current versus case temperature (full cycle).

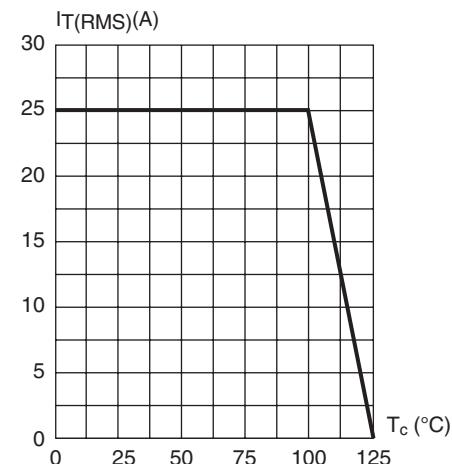


Fig. 3: Relative variation of thermal impedance versus pulse duration.

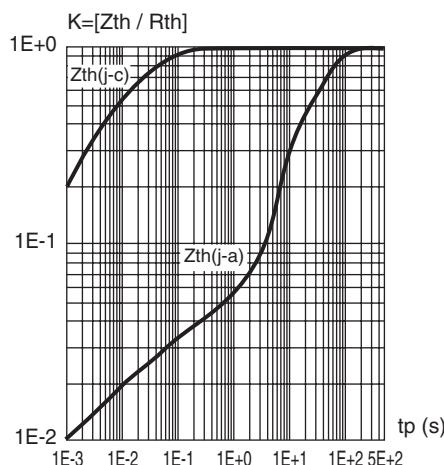


Fig. 5: Surge peak on-state current versus number of cycles

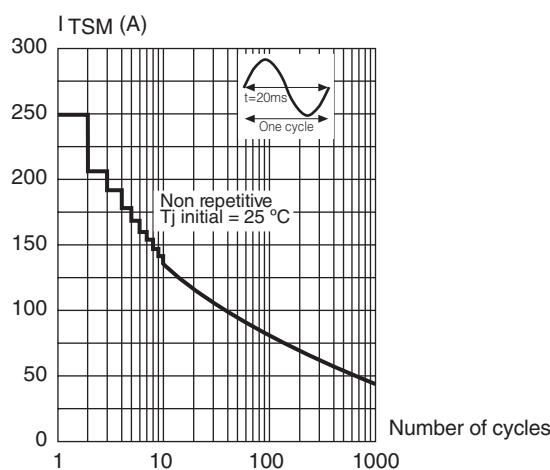


Fig. 4: On-state characteristics (maximum values)

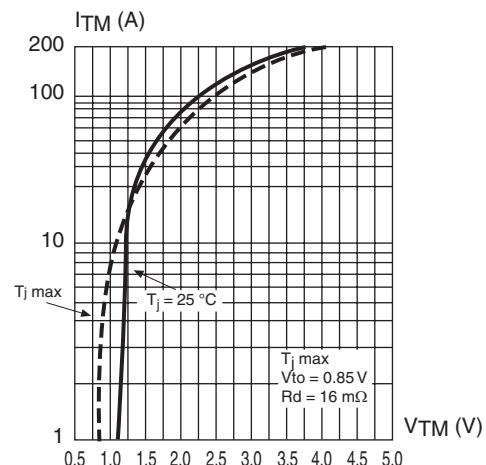
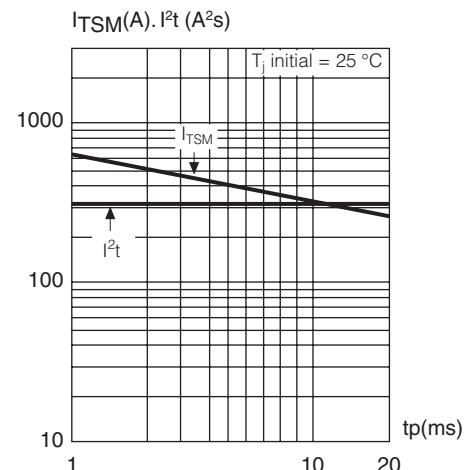


Fig. 6: Non repetitive surge peak on-state current for a sinusoidal pulse with width: $t_p < 20$ ms, and corresponding value of I^2t .



HIGH COMMUTATION TRIAC

Fig. 7: Relative variation of gate trigger current, holding current and latching versus junction temperature (typical values)

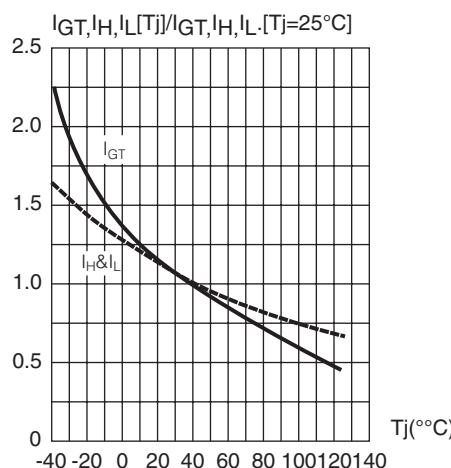
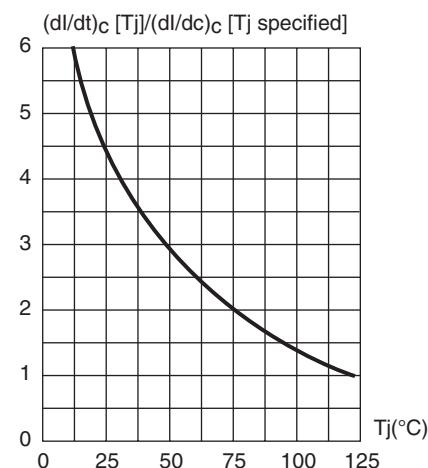
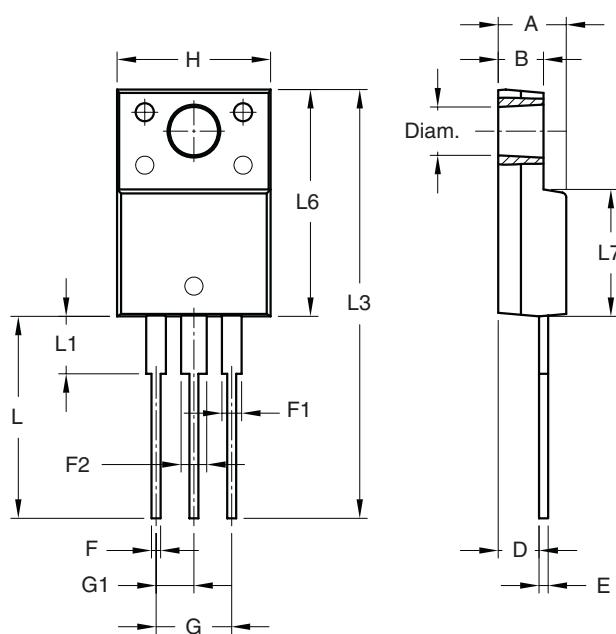


Fig. 8: Relative variation of critical rate of decrease of main current versus junction temperature



PACKAGE MECHANICAL DATA

TO220-F



REF.	DIMENSIONS		
	Millimeters		
	Min.	Nominal	Max.
A	3.55	4.50	4.90
B	2.34	3.00	3.70
D	2.03	2.70	2.96
E	0.35	0.60	0.70
F	0.25	0.60	1.01
F1	0.70	1.30	1.78
F2	0.70	1.70	1.78
G	4.88	5.00	5.28
G1	2.34	2.50	2.74
H	9.65	10.15	10.67
L	12.70	13.35	14.73
L1	2.93	3.75	6.35
L3	26.90	28.35	31.20
L6	14.22	15.00	16.50
L7	8.30	8.40	9.59
Diam.	3.00	3.20	3.28